ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I_R*	T_j = 25°C	$V_R = V_{RRM}$			0.5	mA
	T_j = 100°C				10	
V_F*	I_F = 1A	T_j = 25°C			0.7	V
	I_F = 3A				1	

* Pulse test: $t_p \leq 300\mu s$ $\delta < 2\%$.

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C	T_j = 25°C	V_R = 0		150		pF
	T_j = 25°C	V_R = 5V		40		

Forward current flow in a Schottky rectifier is due to majority carrier conduction. So reverse recovery is not affected by storage charge as in conventional PN junction diodes.

Nevertheless, when the device switches from forward biased condition to reverse blocking state, current is required to charge the depletion capacitance of the diode.

This current depends only of diode capacitance and external circuit impedance. Satisfactory circuit behaviour analysis may be performed assuming that Schottky rectifier consists of an ideal diode in parallel with a variable capacitance equal to the junction capacitance (see fig. 5 page 4/4).

Figure 1. Forward current versus forward voltage at low level (typical values).

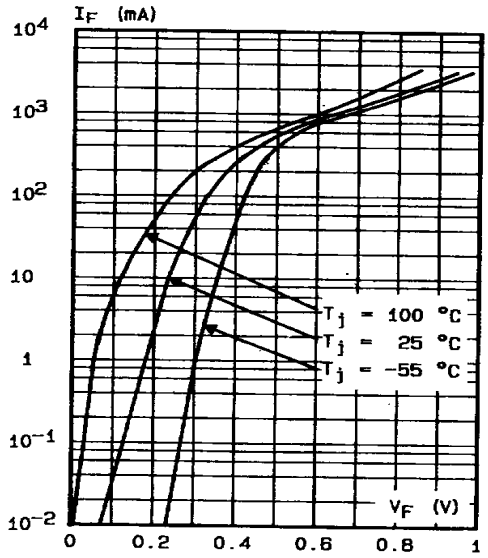


Figure 2. Forward current versus forward voltage at high level (typical values).

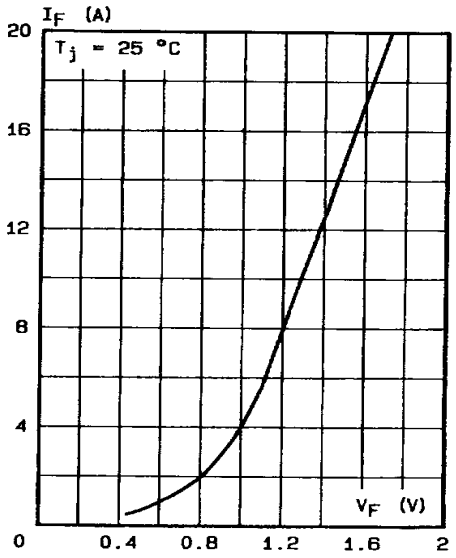


Figure 3. Reverse current versus junction temperature.

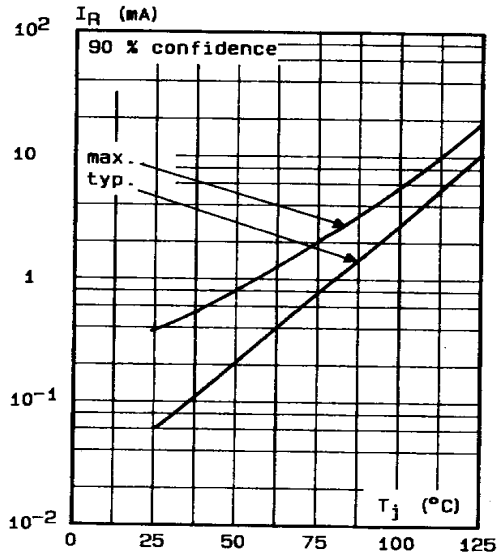


Figure 4. Reverse current versus V_{RRM} in per cent.

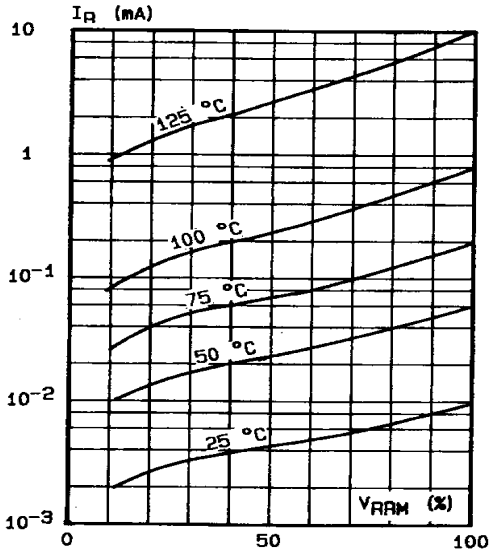


Figure 5. Capacitance C versus reverse applied voltage V_R (typical values)

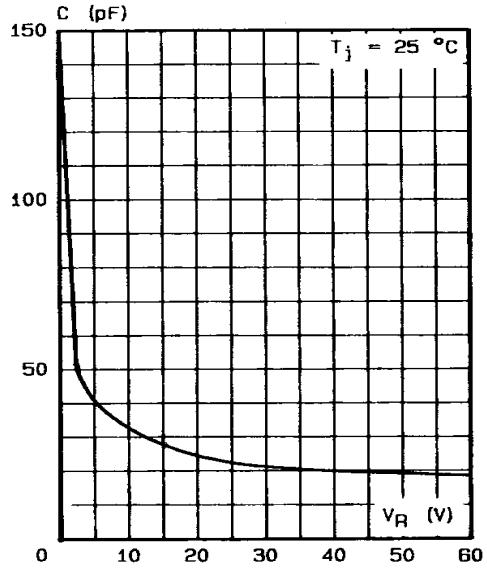


Figure 6. Surge non repetitive forward current for a rectangular pulse with t ≤ 10 ms.

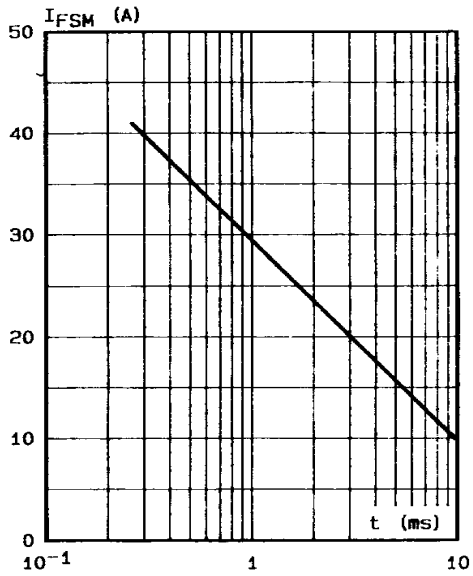
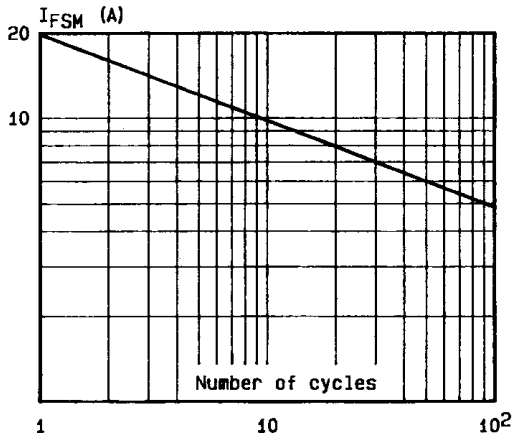
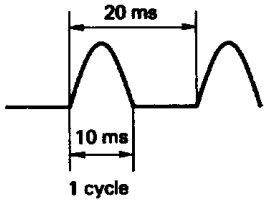


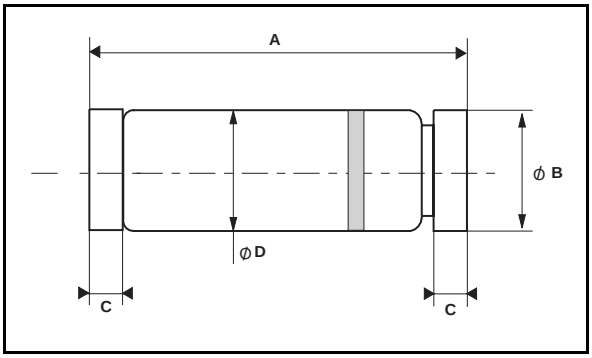
Figure 7. Surge non repetitive forward current versus number of cycles.





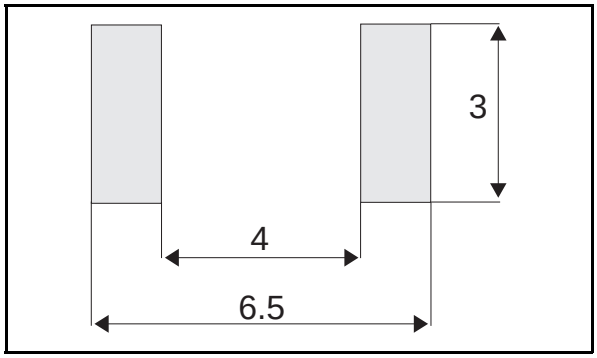
PACKAGE MECHANICAL DATA

MELF Glass



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.80		5.20	0.189		0.205
∅ B	2.50		2.65	0.098		0.104
C	0.45		0.60	0.018		0.024
∅ D		2.50			0.098	

FOOT PRINT DIMENSIONS (Millimeter)



Marking: ring at cathode end.
Weight: 0.15g